

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A light-emitting apparatus, comprising:
a primary light source including a GaN semiconductor light-emitting device with an emission that emits light of a wavelength of 380 nm to 500 nm; said GaN semiconductor light-emitting device including a single reflective layer disposed on a surface of a substrate on which no light-emitting layer is formed; and
a secondary light source including a fluorescent material including that comprises at least one of ZnS:Cu, Au, Al; ZnS:Cu, Al; ZnS:Cu; and Y₂O₂S:Ce,
wherein said ~~secondary light source emits light based on light given from said primary light source so that light of said secondary light source and the light of said primary light source are mixed together to thereby generate light different in luminescent color from the light emitted from said primary light source, and~~
wherein the GaN semiconductor light-emitting device comprises:
a substrate;
a light-emitting layer configured to emit light; and
a single reflection layer positioned closer to the substrate than the light-emitting layer and being configured to reflect light toward a light extracting direction fluorescent material absorbs light of a first wavelength, emitted by said primary light source, and emits light of a second wavelength, which is greater than said first wavelength.
2. (Currently Amended) A light-emitting apparatus according to claim 1, wherein
said fluorescent material is dispersed into ~~a first layer composed of in~~ a light-transmissible material layer, which is disposed above said primary light source,
a part of the said light emitted from by said primary light source is transmitted through said first light-transmissible layer, and
the other another part of the said light emitted from by said primary light source is absorbed by said fluorescent material ~~so that~~, said fluorescent material then emits light, and the said light emitted from by said fluorescent material and the said light emitted from by said primary light source are mixed together, to thereby generate a light, emitted from said light-

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~~emitting apparatus, that is different in luminescent color from the said light emitted from by~~
said primary light source.

3. (Currently Amended) A light-emitting apparatus according to claim 2, wherein
said first light-transmissible layer comprises at least one ~~member selected from the group~~
~~consisting of epoxy resin, silicone resin, urea resin, and glass.~~

4. (Canceled)

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5. (Currently Amended) A light-emitting apparatus according to claim 4 ~~3~~,
wherein a sealing member is ~~provided so that said light-emitting device, disposed above said~~
~~first light-transmissible~~ layer and ~~a part of said lead frame are covered with said sealing~~
member leadframe.

6. (Currently Amended) A light-emitting apparatus according to claim 5, wherein
said sealing member ~~is composed of~~ comprises at least one ~~member selected from the group~~
~~consisting of epoxy resin, silicone resin, urea resin, and glass.~~

7. (Original) A light-emitting apparatus according to claim 5, wherein said
sealing member is shaped like a bullet.

8. (Currently Amended) A light-emitting apparatus according to claim 2, wherein
~~an amount a concentration of said fluorescent material changes continuously or stepwise as~~
~~location of said fluorescent material in within said first light-transmissible layer comes nearer,~~
as a function of distance to said GaN semiconductor light-emitting device.

9. (Currently Amended) A light-emitting apparatus according to claim 5, wherein
said first light-transmissible layer and said sealing member ~~are composed of the same~~
comprise one material.

10. (Currently Amended) A light-emitting apparatus according to claim 2, wherein

~~said GaN semiconductor light-emitting device is of comprises a chip type, and said first layer is formed so as to cover said light-emitting device.~~

11. (Currently Amended) A light-emitting apparatus, comprising:
a primary light source including a GaN semiconductor light-emitting device ~~with an emission that emits light of a wavelength of 380 nm to 500 nm; said GaN semiconductor light-emitting device including a single reflective layer disposed on a surface of a substrate on which no semiconductor layer is formed; and~~
a secondary light source including a fluorescent material ~~including that comprises at least one of ZnS:Eu and Y₂O₂S:Ce,~~
wherein ~~said secondary light source emits light based on light given from said primary light source so that light of said secondary light source and the light of said primary light source are mixed together to thereby generate light different in luminescent color from the light emitted from said primary light source, and~~
wherein ~~the GaN semiconductor light-emitting device comprises:~~
a substrate;
a light-emitting layer configured to emit light; and
a single reflection layer positioned closer to the substrate than the light-emitting layer and being configured to reflect light toward a light extracting direction fluorescent material absorbs light of a first wavelength, emitted by said primary light source, and emits light of a second wavelength, which is greater than said first wavelength.

12. (Currently Amended) A light-emitting apparatus according to claim 11, wherein
said fluorescent material is dispersed into a first layer composed of in a light-transmissible material layer, which is disposed above said primary light source,
a part of the said light emitted from by said primary light source is transmitted through said first light-transmissible layer, and
the other another part of the said light emitted from by said primary light source is absorbed by said fluorescent material so that, said fluorescent material then emits light, and

~~the said light emitted from by said fluorescent material and the said light emitted from by said primary light source are mixed together, to thereby generate a light, emitted from said light-emitting apparatus, that is different in luminescent color from the said light emitted from by said primary light source.~~

13. (Currently Amended) A light-emitting apparatus according to claim 12, wherein said ~~first~~ light-transmissible layer comprises at least one ~~member selected from the group consisting of~~ epoxy resin, silicone resin, urea resin, and glass.

14. (Canceled)

15. (Currently Amended) A light-emitting apparatus according to claim 4 ~~13~~, wherein a sealing member is ~~provided so that said light-emitting device, disposed above said first light-transmissible layer and a part of said lead frame are covered with said sealing member leadframe.~~

16. (Currently Amended) A light-emitting apparatus according to claim 15, wherein said sealing member is ~~composed of~~ comprises at least one ~~member selected from the group consisting of~~ epoxy resin, silicone resin, urea resin, and glass.

17. (Original) A light-emitting apparatus according to claim 15, wherein said sealing member is shaped like a bullet.

18. (Currently Amended) A light-emitting apparatus according to claim 12, wherein ~~an amount~~ a concentration of said fluorescent material changes ~~continuously or stepwise as location of said fluorescent material in within~~ said ~~first~~ light-transmissible layer ~~comes nearer, as a function of distance to said GaN semiconductor light-emitting device.~~

19. (Currently Amended) A light-emitting apparatus according to claim 15, wherein said ~~first~~ light-transmissible layer and said sealing member are ~~composed of the same~~ comprise one material.

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20. (Currently Amended) A light-emitting apparatus according to claim 12, wherein said GaN semiconductor light-emitting device is ~~of a chip type, and said first layer is formed so as to cover said light-emitting device.~~

21. (Currently Amended) A light-emitting apparatus, comprising:
a first light source including a GaN semiconductor light-emitting device ~~configured to emit that emits~~ blue light, said GaN semiconductor light-emitting device including a single reflective layer disposed on a surface of a substrate on which no semiconductor layer is formed;

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a second light source including a first fluorescent material ~~configured to absorb that absorbs~~ light of emitted by said first light source and ~~to emit emits~~ green light;
and

a third light source ~~including a second fluorescent material configured to absorb light of said first light source and to emit that emits~~ red light,

wherein ~~the said blue light of emitted by~~ said first light source, said green light of emitted by said second light source, and said red light of emitted by said third light source are mixed ~~together~~ to thereby generate white light.

22. (Currently Amended) A light-emitting apparatus according to claim 21, wherein said first fluorescent material comprises at least one of ZnS:Cu, Au, Al; ZnS:Cu, Al; ZnS:Cu; ZnS:Mn; ZnS:Eu; $Y_2O_3S:Eu$; and $Y_2O_2S:Ce$.

23. (Canceled)

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25. (Original) A light-emitting apparatus according to claim 21, wherein said third light source includes a semiconductor light-emitting device for emitting red light.

26. (Currently Amended) A light-emitting apparatus according to claim ~~21~~ 41, wherein said ~~first~~ fluorescent material ~~is~~ and said second fluorescent material

are dispersed ~~into~~ in a first light-transmissible layer ~~composed of a light-transmissible material~~, which is disposed above said GaN semiconductor light-emitting device,

a part of the said blue light emitted ~~from~~ by said first light source is transmitted through said first light-transmissible layer, and

~~the other another~~ part of the said blue light emitted ~~from~~ by said first light source is absorbed by said first fluorescent material ~~so that said fluorescent material emits light and the light emitted from said fluorescent material, which emits said green light, and said second fluorescent material, which emits said red light, and the said blue light emitted from by said first light source, said green light emitted by said first fluorescent material, and said red light emitted by said second fluorescent material~~ are mixed together, to thereby generate a light, emitted from said light-emitting apparatus, different in luminescent color from the said blue light emitted from said first light source.

27. (Currently Amended) A light-emitting apparatus according to claim 26, wherein said first light-transmissible layer comprises at least one ~~member selected from the group consisting of epoxy resin, silicone resin, urea resin, and glass.~~

28. (Currently Amended) A light-emitting apparatus according to claim 26, wherein said ~~light-emitting device is fixed to a cup portion of a lead frame, and said first light-transmissible layer is formed so that disposed above said GaN semiconductor light-emitting device fixed to said cup portion is covered with said first layer.~~

29. (Currently Amended) A light-emitting apparatus according to claim 28, wherein a sealing member is ~~provided so that said light-emitting device, disposed above said first light-transmissible layer and a part of said lead frame are covered with said sealing member~~ leadframe.

30. (Currently Amended) A light-emitting apparatus according to claim 29, wherein said sealing member ~~is composed of~~ comprises at least one ~~member selected from the group consisting of epoxy resin, silicone resin, urea resin, and glass.~~

31. (Original) A light-emitting apparatus according to claim 29, wherein said sealing member is shaped like a bullet.

32. (Currently Amended) A light-emitting apparatus according to claim 26, wherein ~~an amount~~ a concentration of at least one of said first fluorescent material and said second fluorescent material changes ~~continuously or stepwise as location of said fluorescent material in within~~ said first light-transmissible layer comes nearer, as a function of distance to said GaN semiconductor light-emitting device.

33. (Currently Amended) A light-emitting apparatus according to claim 29, wherein said first light-transmissible layer and said sealing member ~~are composed of the same~~ comprise one material.

34. (Currently Amended) A light-emitting apparatus according to claim 26, wherein said GaN semiconductor light-emitting device ~~is of~~ comprises a chip type, and said first layer is formed so as to cover said light-emitting device.

35. (Canceled)

36. (Canceled)

37. (Canceled)

38. (Previously Added) The light-emitting apparatus according to claim 1, wherein said substrate of said GaN semiconductor light-emitting device comprises sapphire.

39. (Previously Added) The light-emitting apparatus according to claim 11, wherein said substrate of said GaN semiconductor light-emitting device comprises sapphire.

40. (Previously Added) The light-emitting apparatus according to claim 21, wherein said substrate of said GaN semiconductor light-emitting device comprises sapphire.

41. (New) A light-emitting apparatus according to claim 21, wherein said third light source includes a second fluorescent material that absorbs light emitted by said first light source and emits red light.

42. (New) A light-emitting apparatus, comprising:
a box including a bottom surface including a first electrode and a second electrode;
a primary light source including a GaN semiconductor light-emitting device that emits light of a wavelength of 380 nm to 500 nm and is fixed to one of said first electrode and said second electrode, said GaN semiconductor light-emitting device including a single reflective layer disposed on a surface of a substrate on which no light-emitting layer is formed; and
a secondary light source including a fluorescent material that comprises at least one of ZnS:Cu, Au, Al; ZnS:Cu, Al; and ZnS:Cu,
wherein said fluorescent material absorbs light of a first wavelength, emitted by said primary light source, and emits light of a second wavelength, which is greater than said first wavelength.

43. (New) A display device, comprising a plurality of light-emitting device (LED) units, wherein each of said plurality of LED units comprises:
a red LED;
a green LED;
a blue LED; and
a light-emitting apparatus according to claim 1.

44. (New) A display device, comprising a plurality of light-emitting device (LED) units, wherein each of said plurality of LED units comprises:
a red LED;
a green LED;
a blue LED; and
a light-emitting apparatus according to claim 11.

45. (New) A display device, comprising a plurality of light-emitting device (LED) units, wherein each of said plurality of LED units comprises:

- a red LED;
- a green LED;
- a blue LED; and
- a light-emitting apparatus according to claim 41.

46. (New) A vehicular signal display device comprising a plurality of light-emitting apparatuses according to claim 1, wherein said plurality of light-emitting apparatuses comprise a matrix, a portion of said matrix being controlled by a controller, which turns said portion on or off.

47. (New) A linear light source, comprising:
a box including a bottom surface including a first electrode and a second electrode;
a light-emitting apparatus according to claim 1 that is fixed to one of said first electrode and said second electrode; and
a linear light-guide that extends from said box and said light-emitting apparatus along an optical axis and covers said box and said light-emitting apparatus.

48. (New) A planar light source, comprising:
a box including a bottom surface including a plurality of first electrodes and second electrodes;
a plurality of light-emitting apparatuses according to claim 1 that are fixed to a corresponding one of said plurality of first electrodes and said second electrodes; and
a planar light-guide that extends from said box and said plurality of light-emitting apparatuses perpendicular to said box and covering said box and said plurality of light-emitting apparatuses.

49. (New) A light-emitting apparatus according to claim 1, wherein said fluorescent material is dispersed in a light-transmissible layer that is disposed above a sealing

Serial No. 09/654,501
Docket No. T36-124990/KOH

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member, which is disposed above and focuses said light emitted said GaN semiconductor light-emitting device.

50. (New) A light-emitting apparatus according to claim 41, wherein said first fluorescent material is dispersed in a first light-transmissible layer, which is disposed directly above said GaN semiconductor light-emitting device, and a second fluorescent material is dispersed in a second light-transmissible layer, which is disposed on said first light-transmissible layer.
